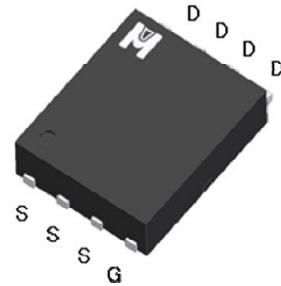


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV _{DSS}	60V
R _{DS(on)} (MAX.)	8mΩ
I _D	60A



UIS, R_g 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS (T_A = 25 °C Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V _{GS}	±20	V
Continuous Drain Current	T _C = 25 °C	I _D	60	A
	T _C = 100 °C		35	
Pulsed Drain Current ^{1,3}		I _{DM}	170	
Avalanche Current		I _{AS}	60	
Avalanche Energy	L = 0.1mH, I _D =60A, R _G =25Ω	E _{AS}	180	mJ
Repetitive Avalanche Energy ²	L = 0.05mH	E _{AR}	90	
Power Dissipation	T _C = 25 °C	P _D	50	W
	T _C = 100 °C		20	
Operating Junction & Storage Temperature Range		T _j , T _{stg}	-55 to 150	°C

100% UIS testing in condition of V_D=30V, L=0.1mH, V_G=10V, I_L=40A, Rated V_{DS}=60V N-CH

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	R _{θJC}		2.5	°C / W
Junction-to-Ambient	R _{θJA}		75	

¹Pulse width limited by maximum junction temperature.

²Duty cycle ≤ 1%

³Pulsed drain current rating is package limited.



ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	60			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	2.0	3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±20V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 48V, V _{GS} = 0V			1	μA
		V _{DS} = 40V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	60			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 40A		6.6	8.0	mΩ
		V _{GS} = 4.5V, I _D = 20A		11	14	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 40A		50		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 25V, f = 1MHz		2869		pF
Output Capacitance	C _{oss}			296		
Reverse Transfer Capacitance	C _{rss}			68		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		2.0		Ω
Total Gate Charge ^{1,2}	Q _g	V _{DS} = 30V, V _{GS} = 10V, I _D = 40A		38		nC
Gate-Source Charge ^{1,2}	Q _{gs}			17		
Gate-Drain Charge ^{1,2}	Q _{gd}			5.2		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = 30V, I _D = 1A, V _{GS} = 10V, R _{GS} = 6Ω		20		nS
Rise Time ^{1,2}	t _r			80		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			120		
Fall Time ^{1,2}	t _f			100		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I _S				60	A
Pulsed Current ³	I _{SM}				170	
Forward Voltage ¹	V _{SD}	I _F = I _S , V _{GS} = 0V			1.3	V
Reverse Recovery Time	t _{rr}	I _F = 25A, dI _F /dt = 100A / μS		30		nS
Reverse Recovery Charge	Q _{rr}				150	

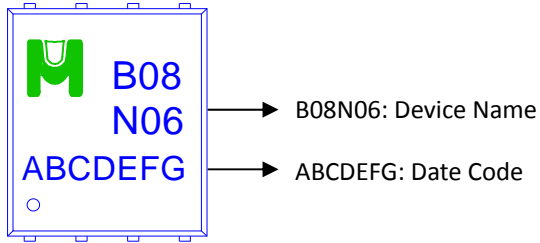
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

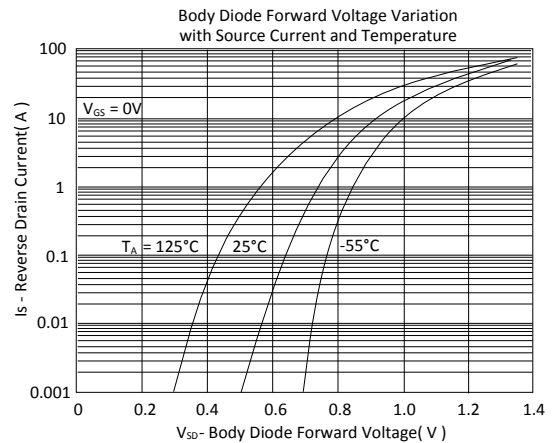
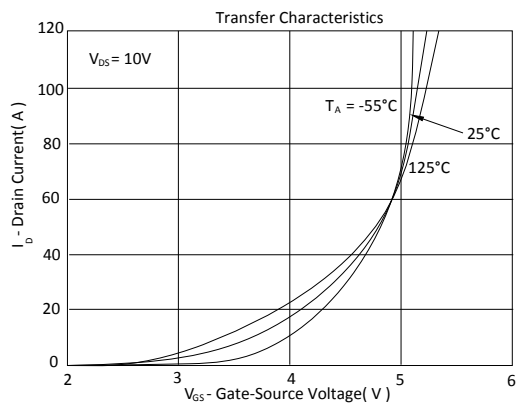
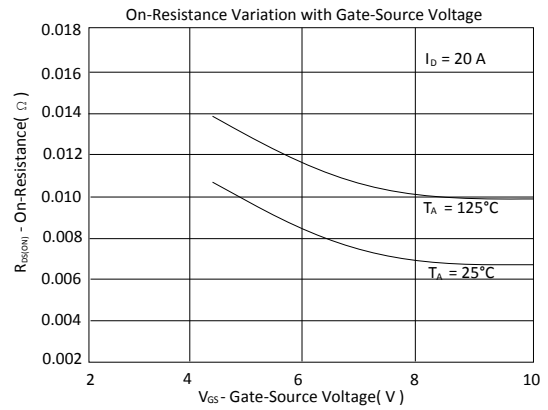
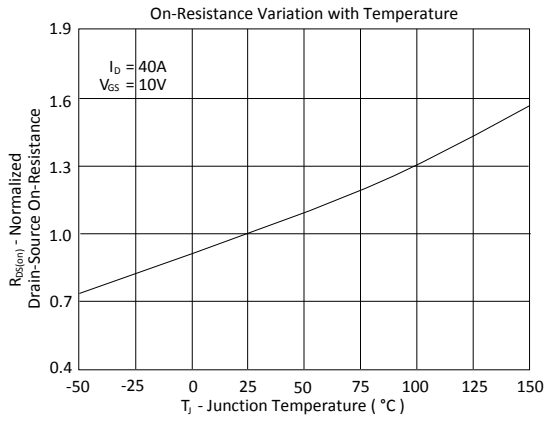
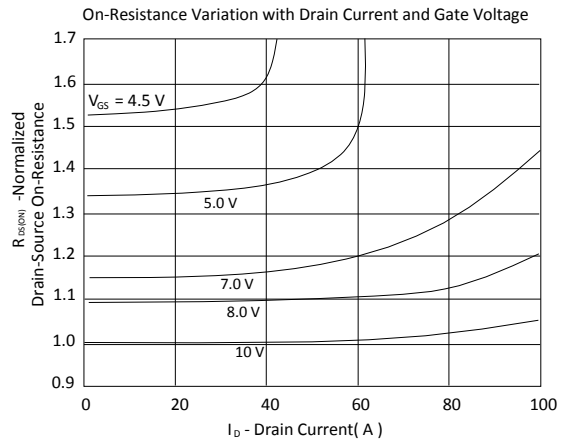
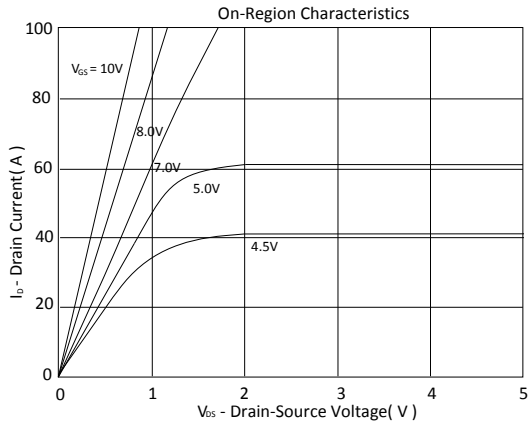
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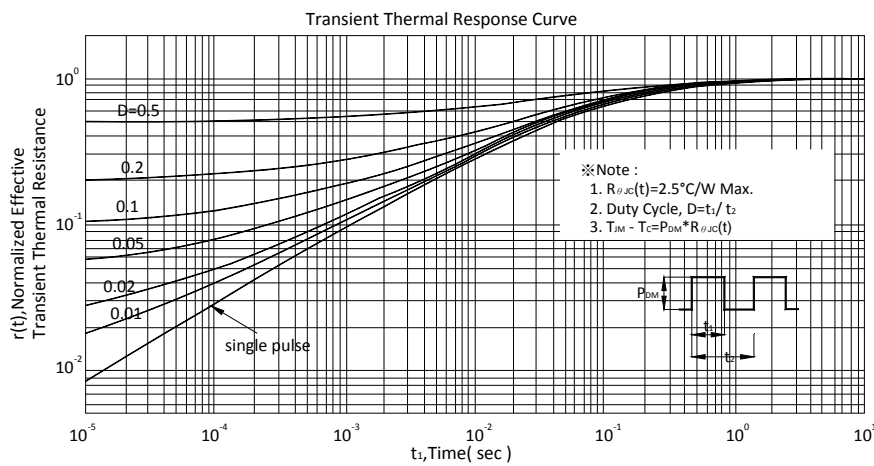
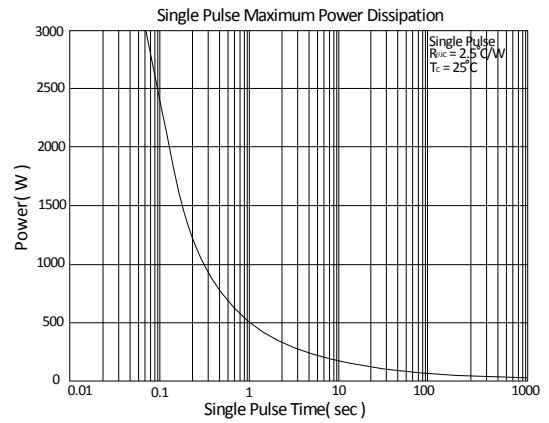
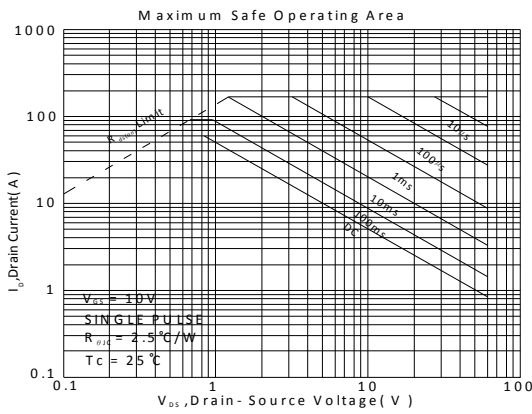
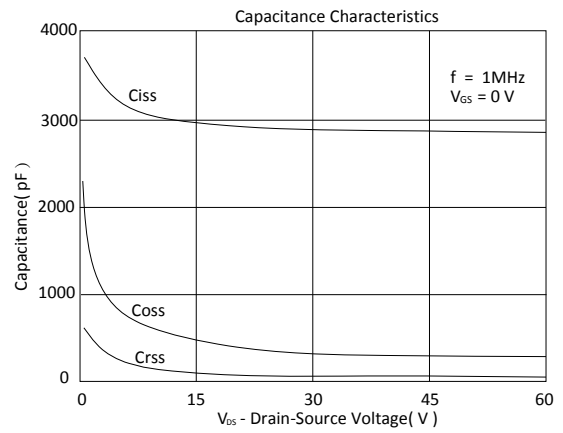
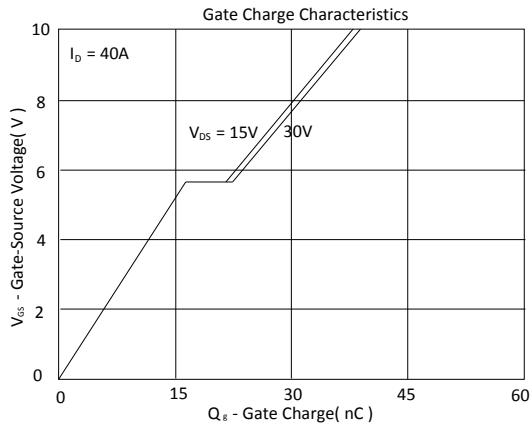
Device Name: EMB08N06H for EDFN 5 x 6





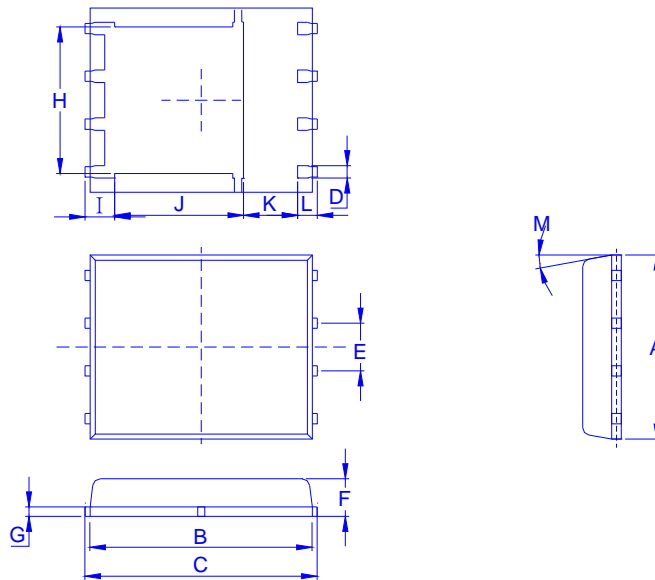
TYPICAL CHARACTERISTICS







Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K	L	M
Min.	4.80	5.50	5.90	0.3		0.85	0.15	3.67	0.41	3.00	0.94	0.45	0°
Typ.					1.27								
Max.	5.30	5.90	6.15	0.51		1.20	0.30	4.54	0.85	3.92	1.7	0.71	12°

Recommended minimum pads

